

7 February 2023

ERRATA | CORRIGENDA

<http://electronicmaterials.usask.ca/corrigenda/>

Only important scientific content related errors are listed.

First printing (April 2017)

Corrections to print version; the e-version is likely to be correct

Page 143: Figure 2.8. The low temperature residual resistivity value shown is $7 \times 10^{-5} \text{ n}\Omega \text{ m}$. This should be $4 \times 10^{-4} \text{ n}\Omega \text{ m}$. The ρ vs T behavior curves at a higher ρ_R .

Page 230: The wavelength 0.0367 nm in Fig. 3.14(b) and 0.0357 nm in the caption should be 0.0123 nm.

Page 245: Equation [3.37], delete the term " $(2m_e/h^2)$ " before " α "

Page 252: Photo on bottom right corner of page, caption should read "An STM image of a silicon crystal surface".

Page 514: Question 5.15, Figure 5.56. "Ga should have 3 electrons and As should have 5 electrons". (This is correct in the 3rd Edition)

Page 555: Last sentence. $V_r^{-1/2}$ should be $V_r^{-1/3}$

Page 556: Equation 6.30, next equation and p557, the equation starting with "slope =", should have N_d in the denominator. All calculations and conclusions are correct. (A typographic error only.)

Page 816: "decreases" in line 3 below Fig. 8.46 should be "increases" and "increases" in the next line should be "decreases".